

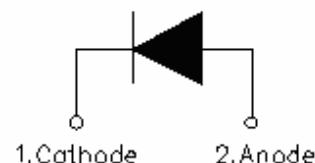
MBRF2045 SCHOTTKY RECTIFIER

Applications:

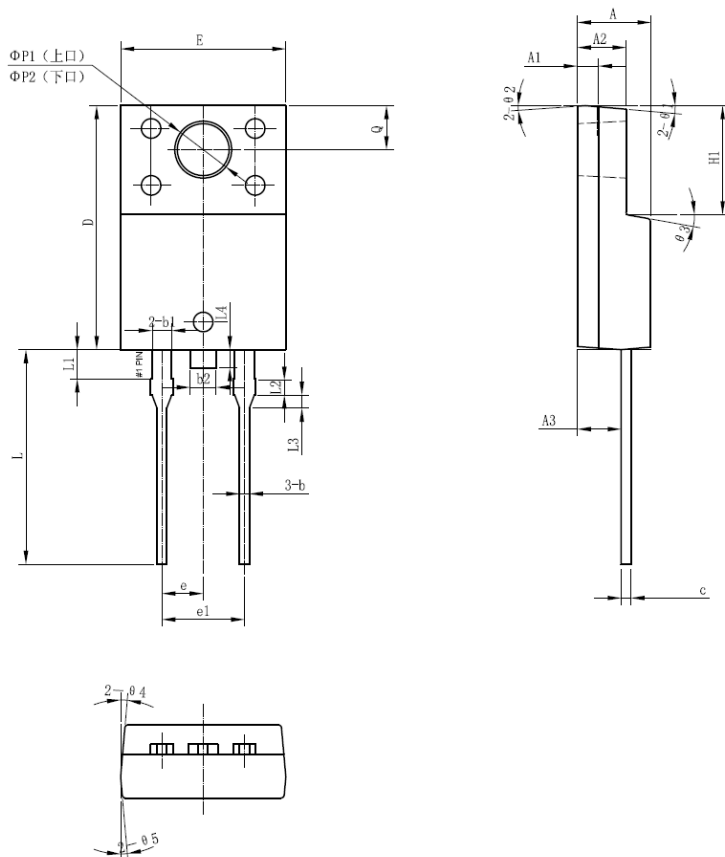
- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Center tap configuration

Features:

- 150 °C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request



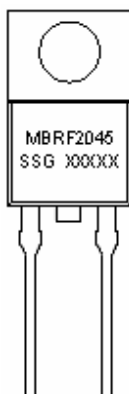
Mechanical Dimensions: In mm



SYMBOL	MIN.	TYP.	MAX.
A	4.30	4.50	4.70
A1	1.10	1.30	1.50
A2	2.80	3.00	3.20
A3	2.50	2.70	2.90
b	0.50	0.60	0.75
b1	1.10	1.20	1.35
b2	1.50	1.60	1.75
c	0.55	0.60	0.75
D	14.80	15.00	15.20
E	9.96	10.16	10.36
e	-	2.55	-
e1	-	5.10	-
H1	6.50	6.70	6.90
L	12.70	13.20	13.70
L1	1.60	1.80	2.00
L2	0.80	1.00	1.20
L3	0.60	0.80	1.00
L4	-	1.10	1.50
ΦP1(上口)	3.30	3.50	3.70
ΦP2(下口)	2.99	3.19	3.39
Q	2.50	2.70	2.90
Θ1		5°	
Θ2		4°	
Θ3		10°	
Θ4		5°	
Θ5		5°	

ITO-220AC(HD)

Marking Diagram:



Where XXXXX is YYWWL

MBR	= Device Type
F	= Package type
20	= Forward Current (20A)
45	= Reverse Voltage (45V)
SSG	= SSG
YY	= Year
WW	= Week
L	= Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
MBRF2045	ITO-220AC (Pb-Free)	50pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	45	V
Max. Average Forward Current	$I_{F(AV)}$	@ $T_C = 105^\circ\text{C}$, Rated V_R	20	A
Max. Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3 ms, half Sine pulse	252	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop*	V_{F1}	@ 20A, Pulse, $T_J = 25\text{ }^{\circ}\text{C}$	0.60	V
	V_{F2}	@ 20A, Pulse, $T_J = 125\text{ }^{\circ}\text{C}$	0.58	V
Max. Reverse Current	I_{R1}	@ $V_R = \text{rated } V_R$ $T_J = 25\text{ }^{\circ}\text{C}$	1	mA
	I_{R2}	@ $V_R = \text{rated } V_R$ $T_J = 100\text{ }^{\circ}\text{C}$	50	mA
Max. Junction Capacitance	C_T	@ $V_R = 5\text{V}$, $T_C = 25\text{ }^{\circ}\text{C}$ $f_{\text{SIG}} = 1\text{MHz}$	900	pF
Typical Series Inductance	L_S	Measured lead to lead 5 mm from package body	8.0	nH
Max. Voltage Rate of Change	dv/dt	-	10,000	V/ μs

* Pulse Width < 300 μs , Duty Cycle <2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature Range	T_J	-	-55 to +150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	-	-55 to +150	$^{\circ}\text{C}$
Maximum Thermal Resistance Junction to Case	$R_{\theta\text{JC}}$	DC operation	1.5	$^{\circ}\text{C/W}$
Maximum Thermal Resistance, Junction to Case(Per package)	$R_{\theta\text{JC}}$	DC operation	50	$^{\circ}\text{C/W}$
Maximum Thermal Resistance, Case to Heat Sink	$R_{\theta\text{CS}}$	Mounting surface, smooth and greased	0.50	$^{\circ}\text{C/W}$
Approximate Weight	wt	-	1.6	g
Case Style	ITO-220AC			

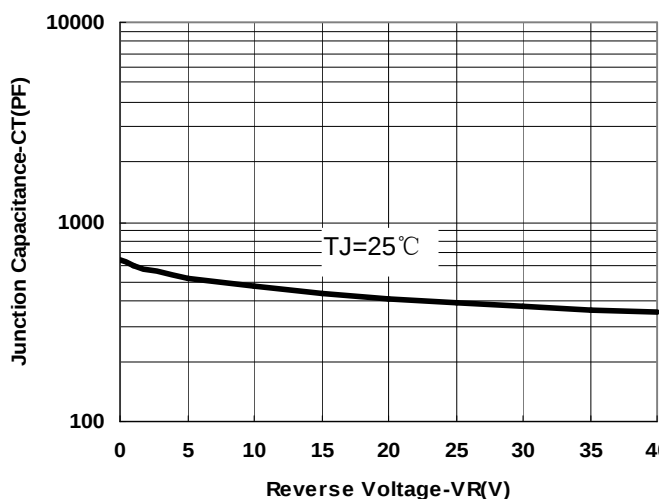


Fig.1-Typical Junction Capacitance

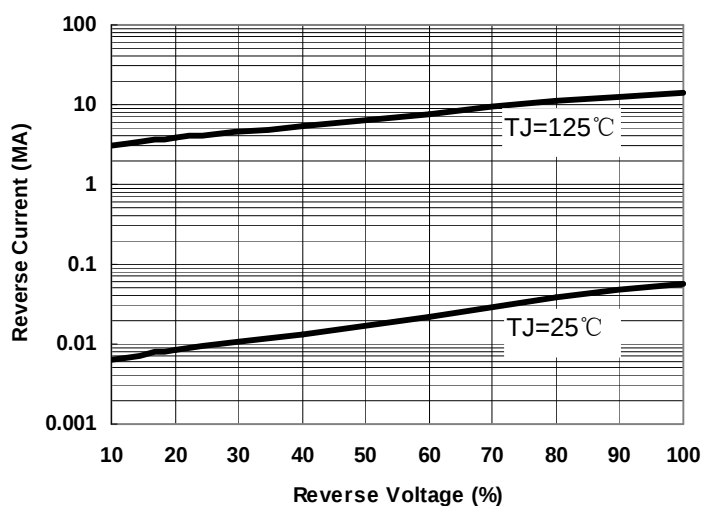


Fig.2-Typical Reverse Characteristics

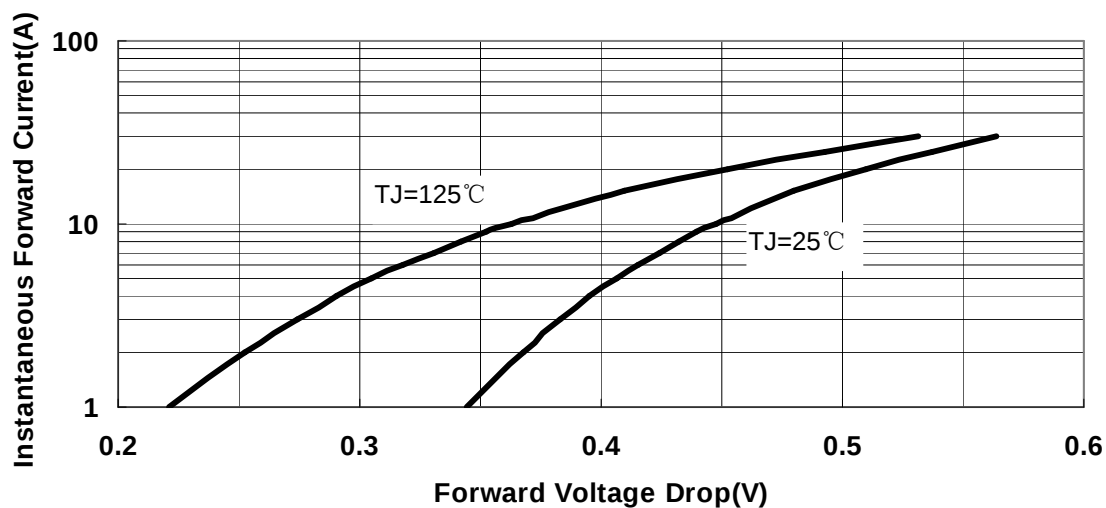


Fig.3-Typical Instantaneous Forward Voltage Characteristics

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